

herein can also be practiced in an embodiment where $W_{\text{FCu}} + W_{\text{FNi}}$ is, for instance, 0.005 μg or greater; and can also provide significant PID-reducing effect in such an embodiment.

[0049]

The polishing method disclosed herein can be preferably implemented in an embodiment where each of W_{FCu} and W_{FNi} is 1 μg or less, preferably 0.6 μg or less, or more preferably 0.3 μg or less, for instance, 0.1 μg or less. When the final stock polishing sub-step is carried out so that both W_{FCu} and W_{FNi} are at or below these values, a silicon substrate with yet fewer PID at the end of the finishing step can be obtained.

[0050]

There are no particular limitations to the concentration of Cu or Ni in the final stock polishing slurry P_F . In a preferable embodiment, at least the Cu concentration or the Ni concentration is 0.3 ppb or lower in the final stock polishing slurry P_F . In other words, the weight of Cu in 1 liter (L) of the final stock polishing slurry P_F is 0.3 μg or less. In a more preferable final stock polishing slurry P_F , at least the Cu concentration or the Ni concentration is 0.1 ppb or lower (more preferably 0.05 ppb or lower, e.g. 0.01 ppb or lower). Such a final stock polishing slurry P_F may show greater PID-reducing effect.

[0051]

The combined concentration of Cu and Ni (or a Cu/Ni combined concentration, hereinafter) in the final stock polishing slurry P_F is, for instance, 1 ppb or lower, preferably 0.5 ppb or lower, more preferably 0.3 ppb or lower, yet more preferably 0.1 ppb or lower, or particularly preferably 0.03 ppb or lower, for instance, 0.02 ppb or lower. A final stock polishing slurry P_F having a lower Cu/Ni combined concentration may exhibit greater PID-reducing effect. The smaller the Cu/Ni combined concentration is, the greater the effect is; or it can be below the detection limit. From the standpoint of the cost-effectiveness, productivity, etc., the polishing method disclosed herein can also be practiced in an embodiment where the Cu/Ni combined concentration is, for instance, 0.001 ppb or higher; and can also provide significant PID-reducing effect in such an embodiment.

[0052]

The polishing method disclosed herein can be preferably implemented in an embodiment where each of the Cu and Ni concentrations in the final stock polishing slurry P_F is preferably 0.3 ppb or lower, more preferably 0.1 ppb or lower, or yet more